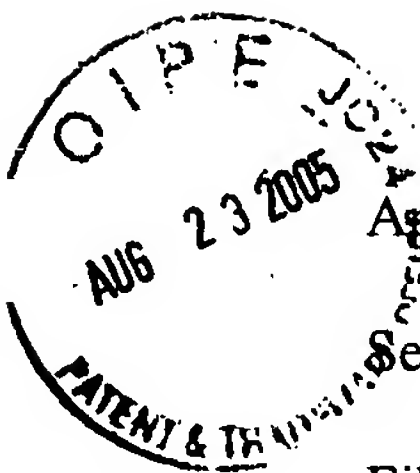


TFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicant: Chien-Chao Huang, et al.  
 Serial No.: 10/710,012  
 Filed: June 11, 2004  
 For: Improved Cobalt Silicidation  
 Process for Substrates with a  
 Germanium Layer

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Docket No.: 2001.1531 / 24061.439  
 Examiner: Matthew C. Landau  
 Art Unit: 2815  
 Conf. No.: 4011

**RESPONSE TO RESTRICTION REQUIREMENT**

Commissioner for Patents  
 Mail Stop: Amendment  
 PO Box 1450  
 Alexandria, VA 22313-1450

Dear Sir:

The present paper is being submitted in response to the Restriction Requirement Office Action dated July 28, 2005 in the above-identified application.

**Election of Claims** begins on page 2 of this paper.

**Amendments to the Claims** are reflected in the Listing of Claims which begins on page 3 of this paper.

**Remarks** begin on page 9 of this paper.

**I. Election**

In the Office Action mailed July 28, 2005, the Examiner alleges that the application contains claims directed to two inventions and, thus, required restriction of either:

Group I: Claims 30-33, drawn to a semiconductor device; and

Group II: Claims 1-29, drawn to a method of making a semiconductor device;

In response, Applicants hereby elect Group II, corresponding to claims 1-29. Applicants' election is made with traverse on the grounds that the embodiments delineated by the Examiner are not patentably distinct and therefore constitute a single invention concept.